

70A, 60V, 0.014 Ohm, N-Channel Power MOSFETs

These are N-Channel power MOSFETs manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI circuits, gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers and relay drivers. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA49007.

Ordering Information

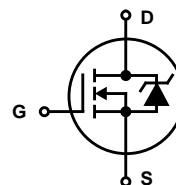
PART NUMBER	PACKAGE	BRAND
RFG70N06	TO-247	RFG70N06
RFP70N06	TO-220AB	RFP70N06
RF1S70N06SM	TO-263AB	F1S70N06

NOTE: When ordering use the entire part number. Add the suffix 9A to obtain the TO-263AB variant in tape and reel, e.g. RF1S70N06SM9A.

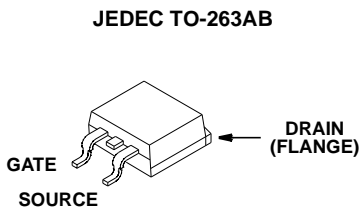
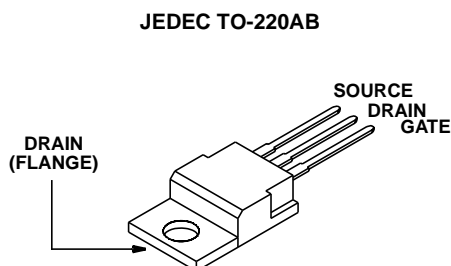
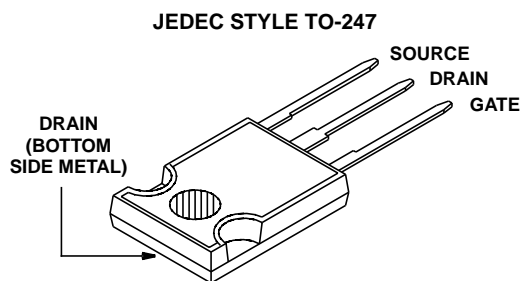
Features

- 70A, 60V
- $r_{DS(on)} = 0.014\Omega$
- Temperature Compensated PSPICE® Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve (Single Pulse)
- 175°C Operating Temperature
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging



RFG70N06, RFP70N06, RF1S70N06SM

Absolute Maximum Ratings

$T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

Drain to Source Voltage (Note 1)	V_{DS}
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	V_{DGR}
Continuous Drain Current	I_D
Pulsed Drain Current (Note 3)	I_{DM}
Gate to Source Voltage	V_{GS}
Single Pulse Avalanche Rating	E_{AS}
Power Dissipation	P_D
Linear Derating Factor	
Operating and Storage Temperature	T_J, T_{STG}
Maximum Temperature for Soldering	
Leads at 0.063in (1.6mm) from Case for 10s	T_L
Package Body for 10s, See Techbrief 334	T_{pkg}

RFG70N06, RFP70N06 RF1S70N06SM	UNITS
60	V
60	V
70	A
Refer to Peak Current Curve	
± 20	V
Refer to UIS Curve	A
150	W
1.0	$W/^{\circ}\text{C}$
-55 to 175	$^{\circ}\text{C}$
300	$^{\circ}\text{C}$
260	$^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- $T_J = 25^{\circ}\text{C}$ to 150°C .

Electrical Specifications

$T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$ (Figure 11)	60	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$ (Figure 10)	2	-	4	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
		$V_{DS} = 0.8 \times \text{Rated } BV_{DSS}$, $T_C = 150^{\circ}\text{C}$	-	-	25	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 70\text{A}$, $V_{GS} = 10\text{V}$ (Figure 9)	-	-	0.014	Ω
Turn-On Time	$t_{(ON)}$	$V_{DD} = 30\text{V}$, $I_D \approx 70\text{A}$, $R_L = 0.43\Omega$, $V_{GS} = 10\text{V}$, $R_{GS} = 2.5\Omega$ (Figure 13)	-	-	125	ns
Turn-On Delay Time	$t_{d(ON)}$		-	12	-	ns
Rise Time	t_r		-	50	-	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	40	-	ns
Fall Time	t_f		-	15	-	ns
Turn-Off Time	$t_{(OFF)}$		-	-	125	ns
Total Gate Charge	$Q_{g(TOT)}$	$V_{GS} = 0\text{V}$ to 20V	-	185	215	nC
Gate Charge at 10V	$Q_{g(10)}$	$V_{GS} = 0\text{V}$ to 10V	-	100	115	nC
Threshold Gate Charge	$Q_{g(TH)}$	$V_{GS} = 0\text{V}$ to 2V	-	5.5	6.5	nC
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$ (Figure 12)	-	3000	-	pF
Output Capacitance	C_{OSS}		-	900	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	300	-	pF
Thermal Resistance, Junction to Case	$R_{\theta JC}$		-	-	1.0	$^{\circ}\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	TO-220 and TO-263	-	-	62	$^{\circ}\text{C/W}$
		TO-247	-	-	30	$^{\circ}\text{C/W}$

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 70\text{A}$		-	1.5	V
Reverse Recovery Time	t_{rr}	$I_{SD} = 70\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$		-	125	ns

NOTES:

- Pulse test: pulse width $\leq 300\text{ms}$, duty cycle $\leq 2\%$.
- Repetitive rating: pulse width is limited by maximum junction temperature. See Transient Thermal Impedance curve (Figure 3) and Peak Current Capability Curve (Figure 5).

Typical Performance Curves Unless Otherwise Specified

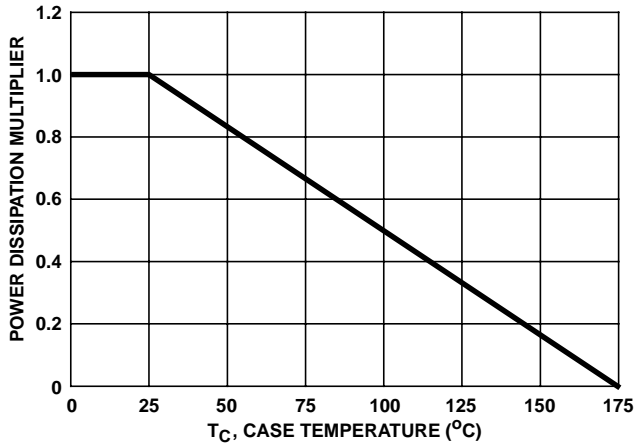


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

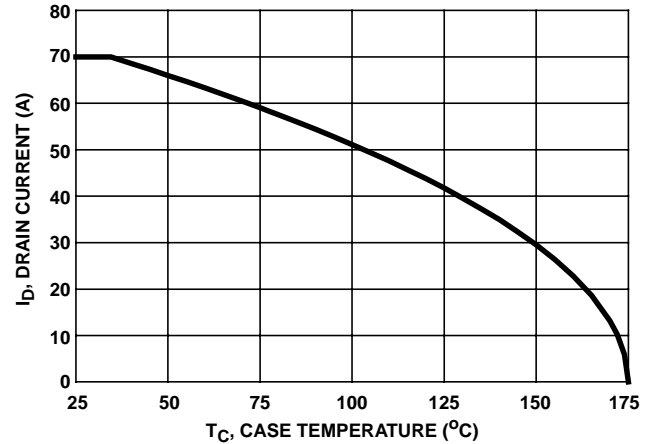


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

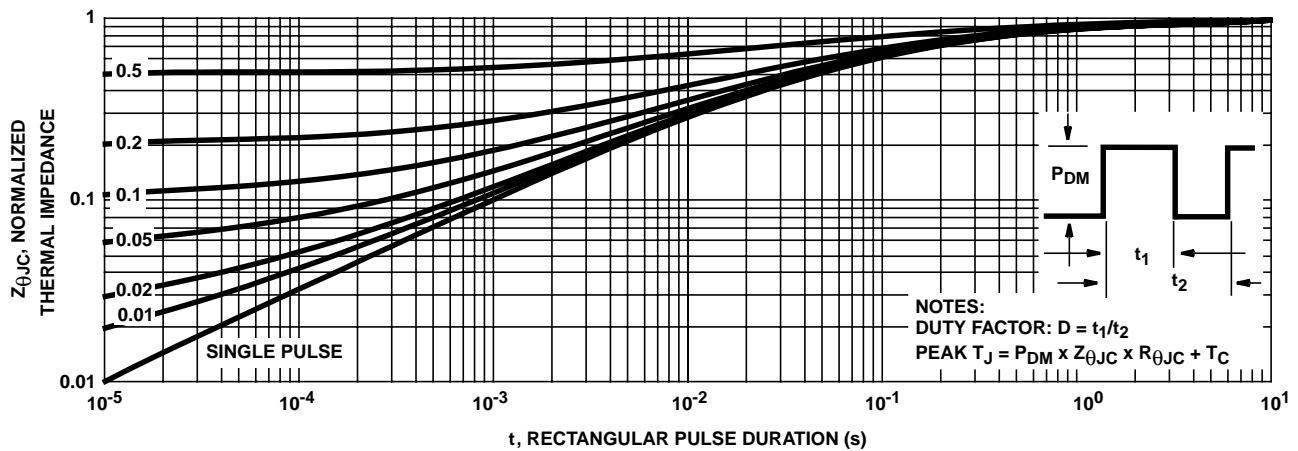


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

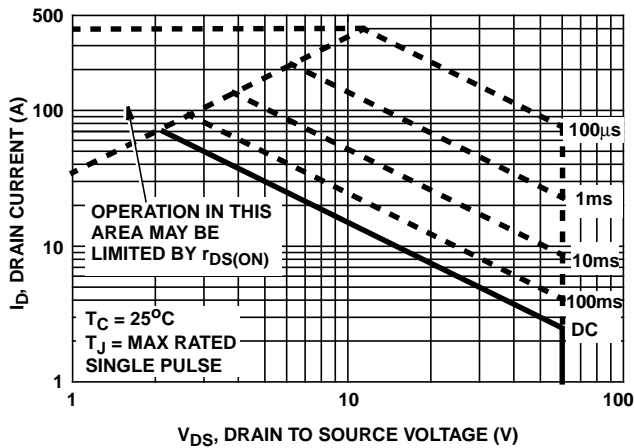


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

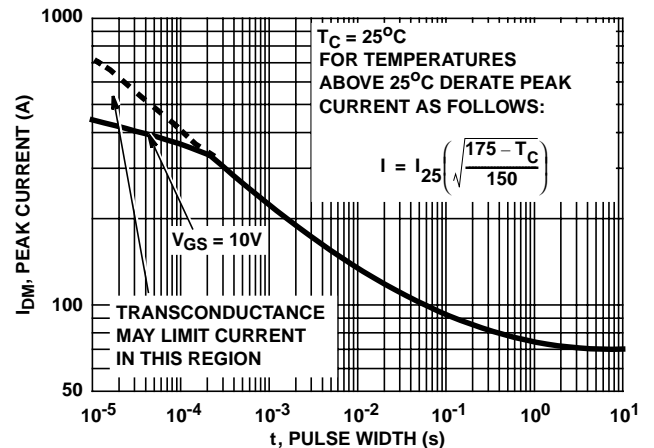


FIGURE 5. PEAK CURRENT CAPABILITY